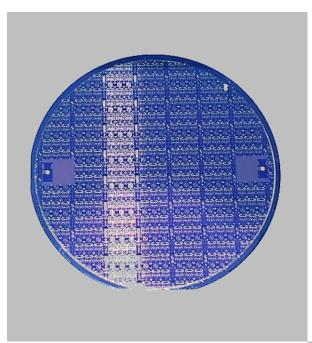
Foundry Process Data Sheet



ULRC-20



Passive process

Description

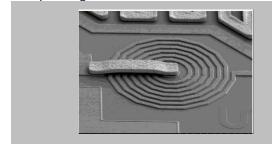
ULRC-20 is a GaAs passive process gathering GaAs properties: high resistivity, good isolation and high dielectric constant. These advantages are associated with high voltage MIM capacitors and high current density metal lines. This process is optimized for reproducibility, power handling, low losses, up to high frequency and for high volume / high yield production.

ULRC-20 allows very diverse passive circuit design including accurate microwave filters, RF power combiners, microwave baluns, matching elements, low losses lines; power bar input and output matching circuits.

ULRC-20 is widely recommended to design hybrid microwave circuits for amplifier modules used into antenna transmitters and receivers such as Radars, Telecom and Space Communication systems.

Main Features

- Fully optical process
- M.I.M. capacitors
- Inductors
- Metallic resistors
- TaN and TiWSi resistors
- Via holes through the GaAs substrate
- Thick Au lines
- Wafer thickness: 100µm
- Wafer diameter: 4"
- Optional coating compatible with plastic package



Metal 2 – thick Au metal: - transmission lines and interconnection - gir bridge technology - top electrode for MIM capacitors - optional BCB protection layer - optional BCB protection layer - optional BCB protection layer - transmission lines and interconnection - bottom electrode for MIM capacitors - line for inductor - transmission lines and interconnection - bottom electrode for MIM capacitors - line for inductor - resistors: - refractory metal - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - bottom electrode for MIM capacitors - transmission lines and interconnection - transmission lines and i

Design Kit Characteristics

- Available for ADS from Keysight,
- Schematic entry with autolayout generation
- Scalable models
- Data for spread analysis

Ref.: 210423210423_DS GaAs ULRC_1114 - 23 Apr 21

Specifications subject to change without notice

Electrical Characteristics

| ELEMENT / Parameters | Min | Тур | Max | Units | Conditions |
|-----------------------------|-----|-------|------|----------|------------|
| | | | | | |
| INDUCTOR | | | | | |
| Inductance | 0.1 | | 12.7 | nH | |
| Via hole diameter | | 30x30 | | um | |
| Substrate thickness | | 100 | | μm | |
| | | | | | |
| Tan resistor / | | | | | |
| sheet resistance | 26 | 30 | 34 | Ω/square | |
| | | | | | |
| TiWSi RESISTOR / | | | | | |
| sheet resistance | 800 | 1000 | 1200 | Ω/square | |
| | | | | | |
| MIM CAPACITOR / | | | | | |
| Density | 160 | 175 | 190 | pF/mm2 | @1MHz |

Ordering Information

Voltage

Visit our Website for more info: https://www.ums-rf.com

Please contact our Sales at: marketing.sales@ums-rf.com & Tel: +33 1 69 86 32 00

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